

Dispersion of the Index of Refraction Near the Absorpti

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Citation Report

#	ARTICLE	IF	CITATIONS
1	INTERNAL FREQUENCY MODULATION OF GaAs JUNCTION LASERS BY CHANGING THE INDEX OF REFRACTION THROUGH ELECTRON INJECTION. <i>Applied Physics Letters</i> , 1964, 5, 198-199.	3.3	19
2	Optoelectronics as applied to functional electronic blocks. <i>Proceedings of the IEEE</i> , 1964, 52, 1529-1536.	21.3	14
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10	Optical Dispersion of Lead Sulfide in the Infrared. <i>Physical Review</i> , 1965, 140, A1283-A1291.	2.7	37
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20	Changes of Refractivity and Nonlinear Optical Phenomena by Franz-Keldysh Effect of Silicon. <i>Japanese Journal of Applied Physics</i> , 1966, 5, 1132-1139.	1.5	0
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